

# **Device Modeling Report**

COMPONENTS: Power MOSFET (Professional)  
PART NUMBER: SSM3J15FS  
MANUFACTURER: TOSHIBA  
Body Diode (Professional) / ESD Protection Diode

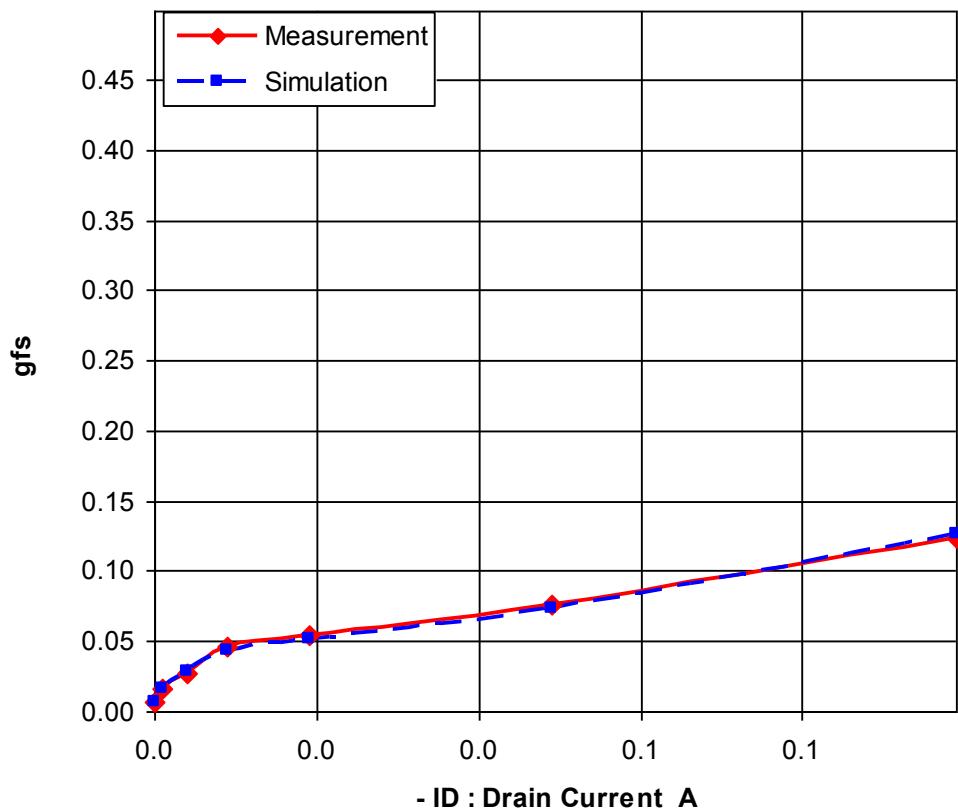


## MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

## Transconductance Characteristic

Circuit Simulation Result

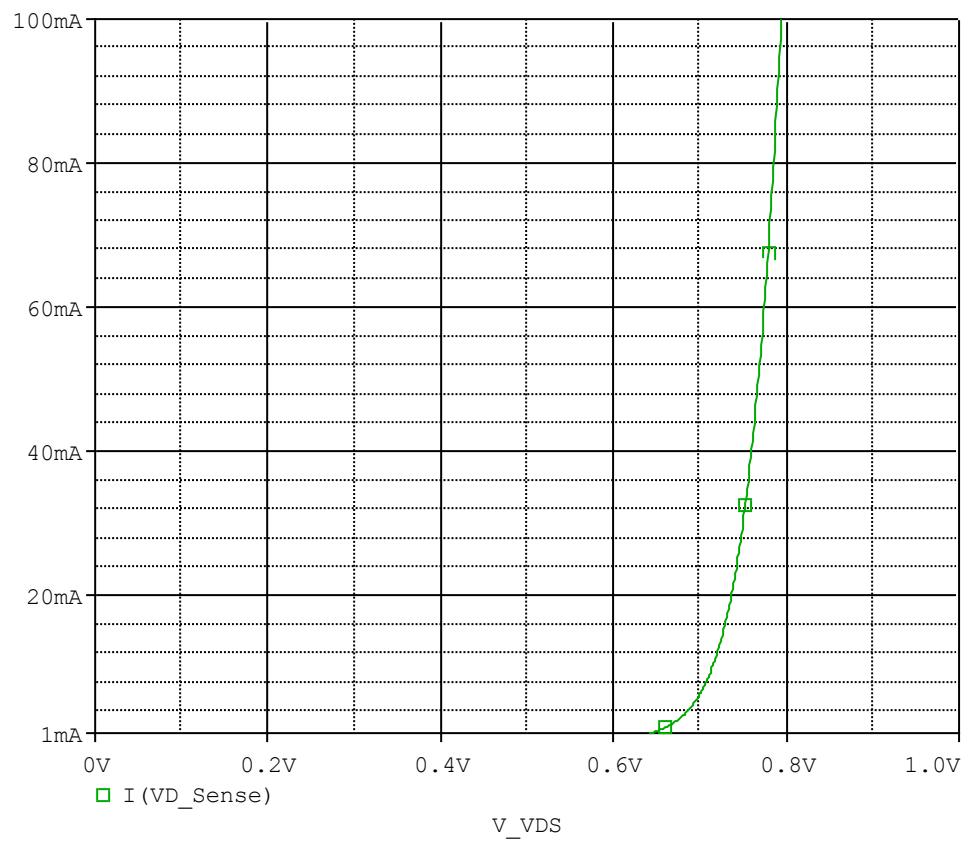


Comparison table

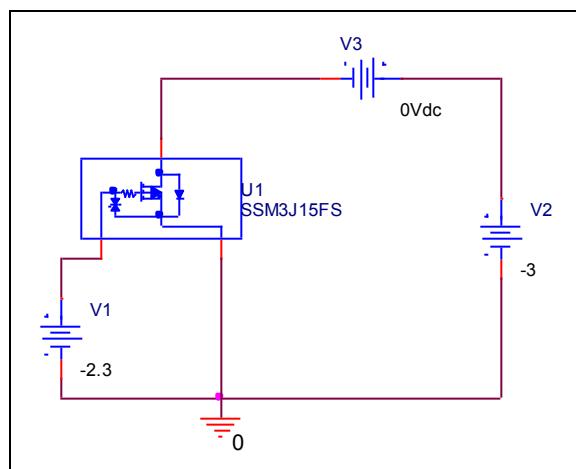
- Id(mA)	gfs		Error(%)
	Measurement	Simulation	
0.0010	0.0082	0.0080	-2.4390
0.0020	0.0173	0.0170	-1.7341
0.0050	0.0280	0.0290	3.5714
0.0100	0.0470	0.0450	-4.2553
0.0200	0.0550	0.0530	-3.6364
0.0500	0.0770	0.0740	-3.8961
0.1000	0.1250	0.1280	2.4000

## V<sub>gs</sub>-I<sub>d</sub> Characteristic

Circuit Simulation result

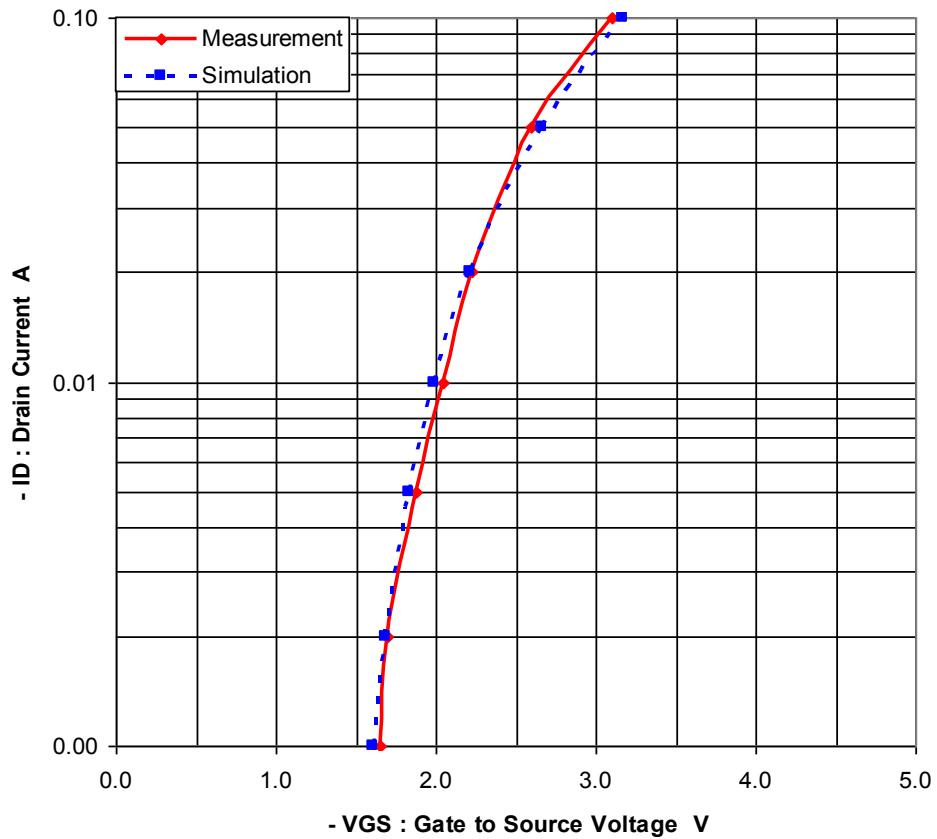


Evaluation circuit



## Comparison Graph

Circuit Simulation Result

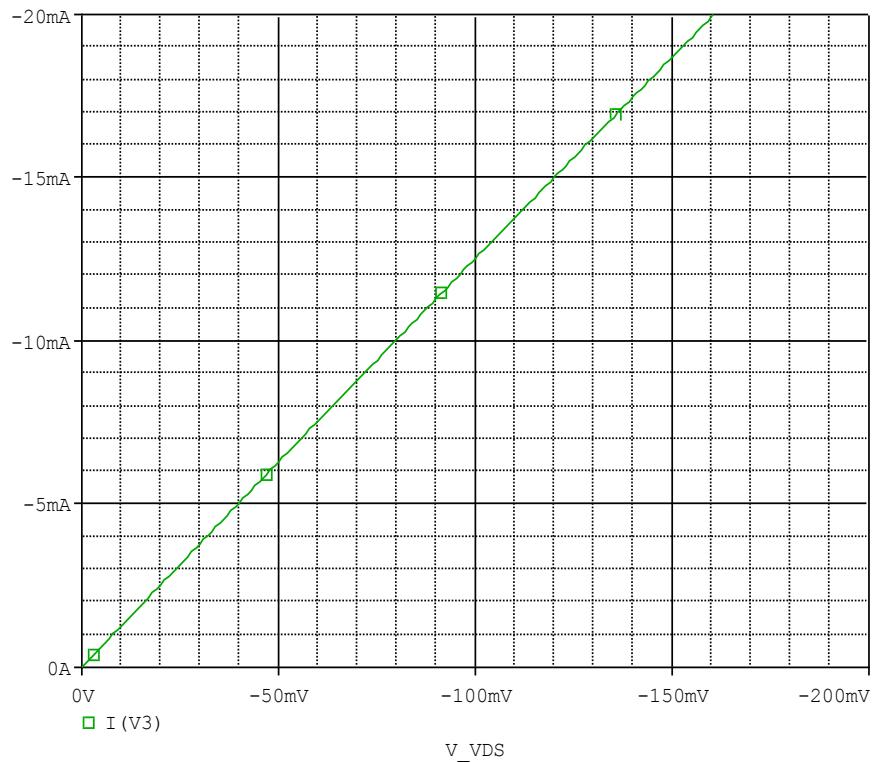


Simulation Result

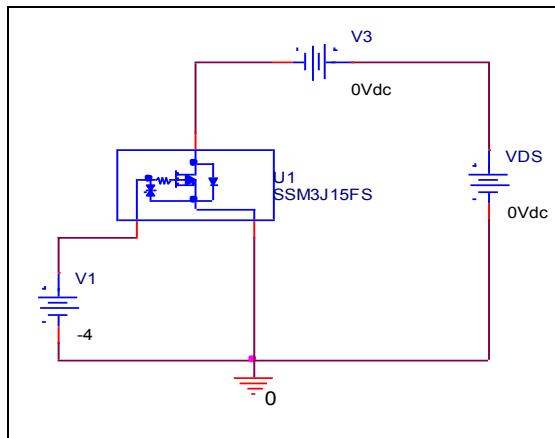
- ID (mA)	- V <sub>GS</sub> (V)		Error (%)
	Measurement	Simulation	
0.001	1.650	1.610	-2.424
0.002	1.700	1.685	-0.882
0.005	1.880	1.829	-2.713
0.010	2.050	1.988	-3.024
0.020	2.220	2.210	-0.450
0.050	2.600	2.658	2.231
0.100	3.100	3.170	2.258

## Rds(on) Characteristic

### Circuit Simulation result



### Evaluation circuit

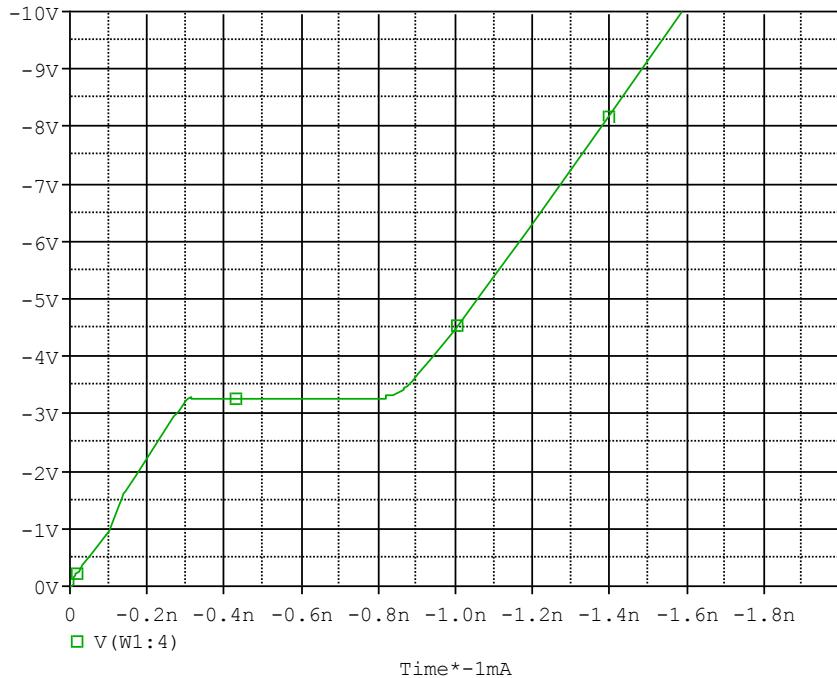


### Simulation Result

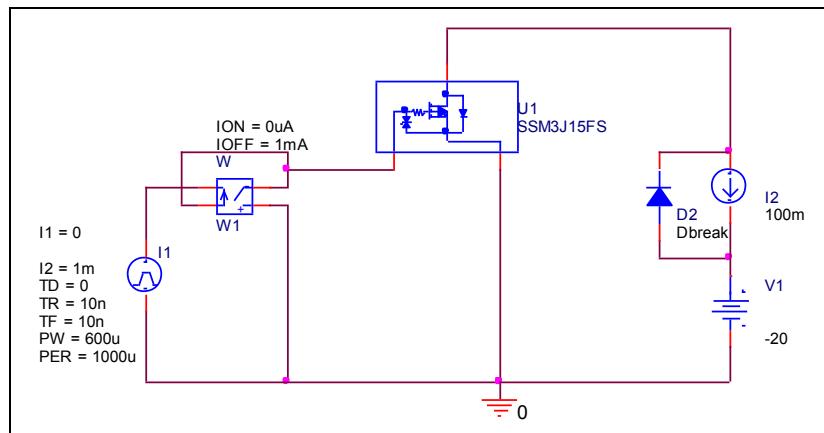
$I_D = -10\text{mA}, V_{GS} = -4\text{V}$	Measurement	Simulation	Error (%)
$R_{DS} (\text{on}) \Omega$	8.000	7.962	-0.475

## Gate Charge Characteristic

### Circuit Simulation result



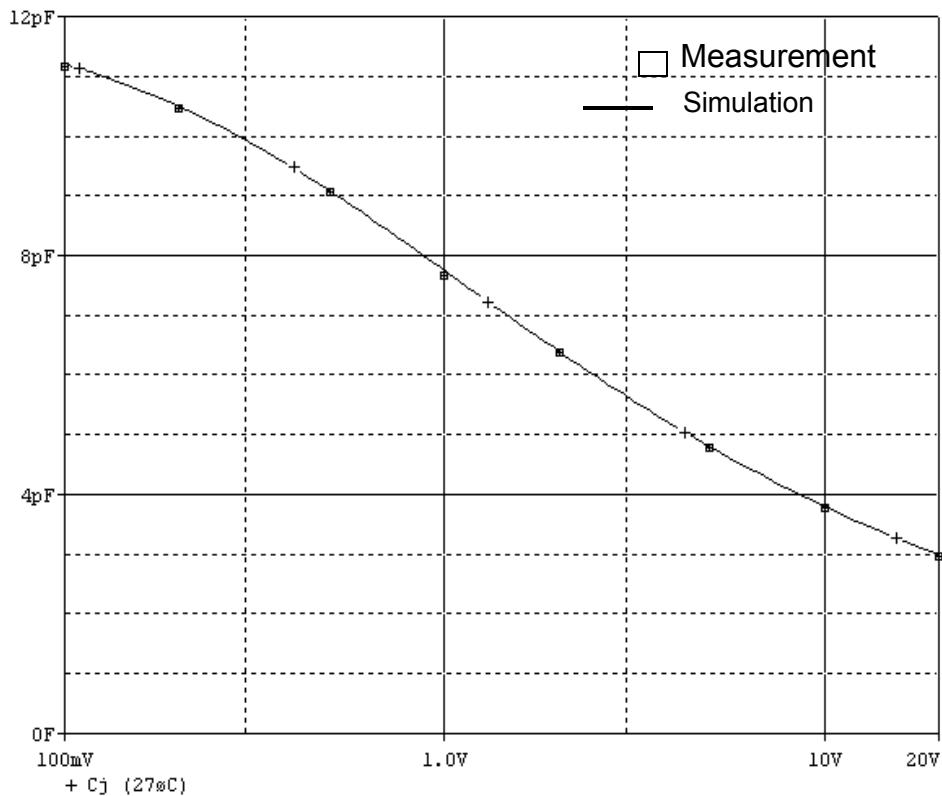
### Evaluation circuit



### Simulation Result

$V_{DD}=-20V, I_D=-100mA, V_{GS}=-10V$	Measurement	Simulation	Error (%)
$Q_{GS}(\text{nC})$	<b>0.300</b>	<b>0.301</b>	<b>0.333</b>
$Q_{GD}(\text{nC})$	<b>0.500</b>	<b>0.503</b>	<b>0.600</b>
$Q_G(\text{nC})$	<b>1.600</b>	<b>1.589</b>	<b>-0.688</b>

## Capacitance Characteristic

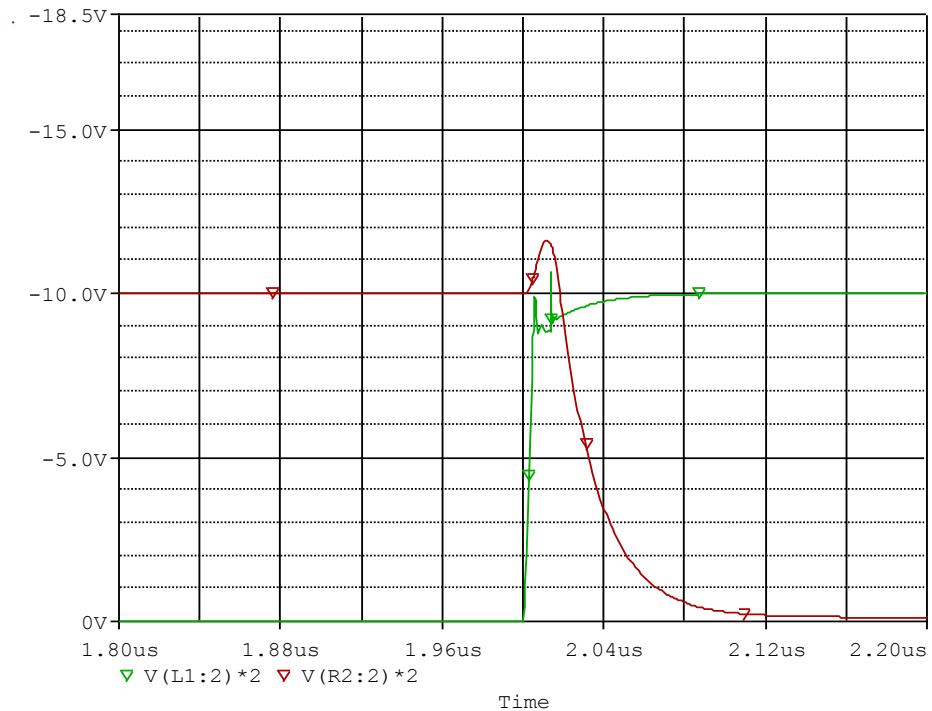


### Simulation Result

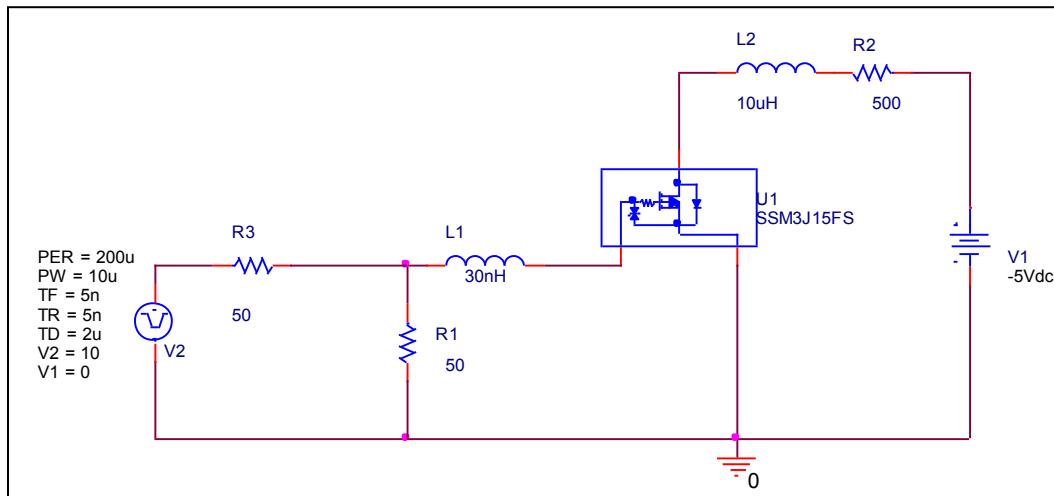
$V_{DS}(V)$	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.100	11.200	11.206	0.054
0.200	10.500	10.490	-0.095
0.500	9.100	9.070	-0.330
1.000	7.700	7.750	0.649
2.000	6.400	6.391	-0.141
5.000	4.800	4.808	0.167
10.000	3.800	3.815	0.395
20.000	3.000	2.996	-0.133

## Switching Time Characteristic

### Circuit Simulation result



### Evaluation circuit

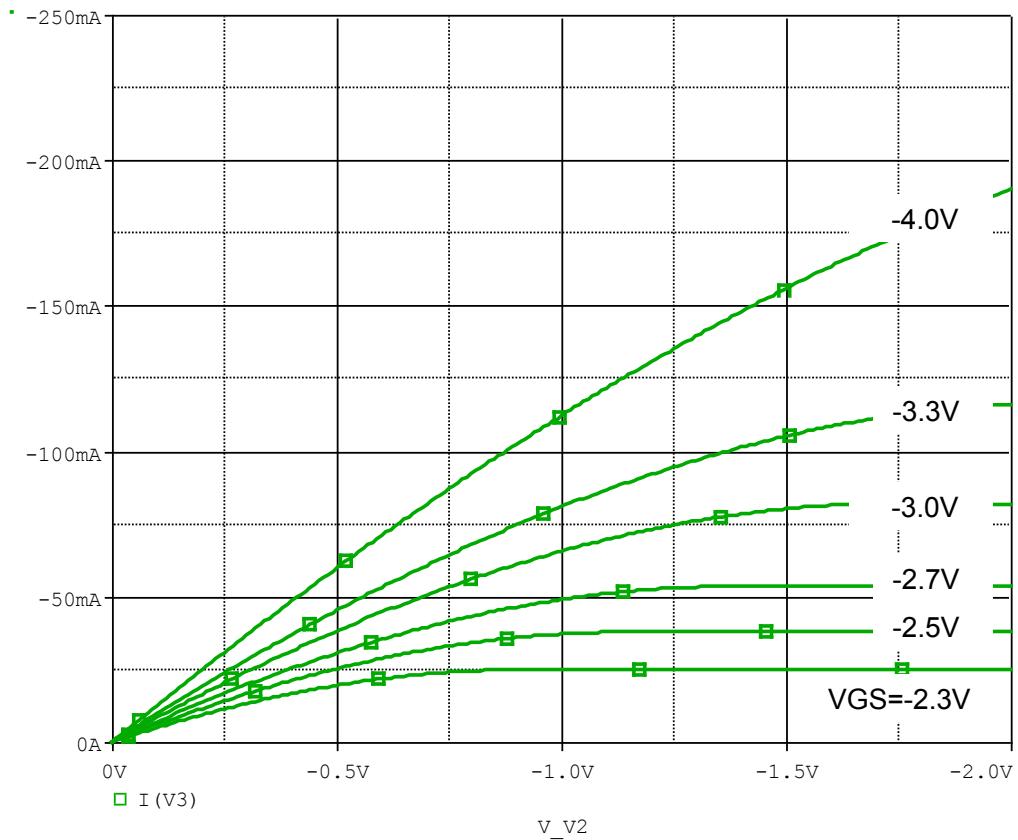


### Simulation Result

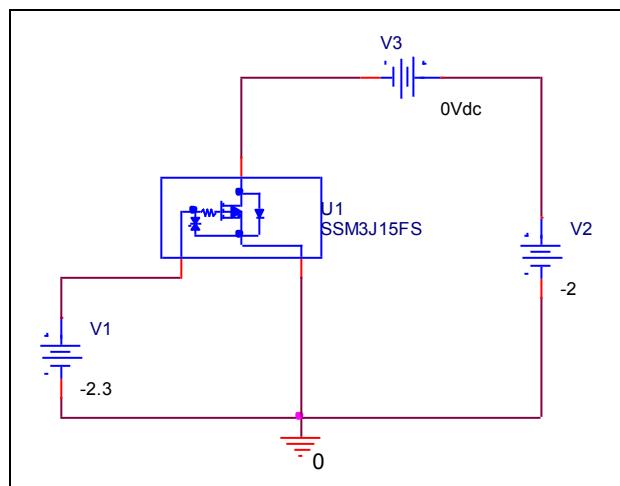
$I_D = -10\text{mA}$ , $V_{DD} = -5\text{V}$ $V_{GS} = -5\text{V}$	Measurement	Simulation	Error(%)
Ton(ns)	65.000	65.367	0.565

## Output Characteristic

Circuit Simulation result

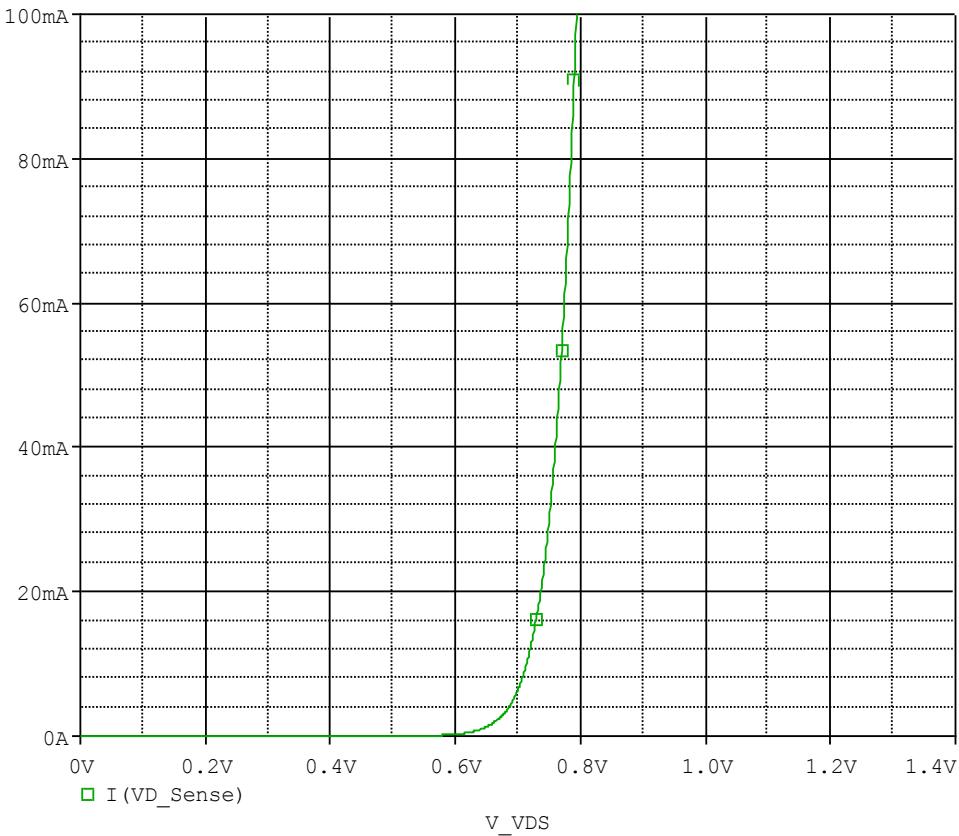


Evaluation circuit

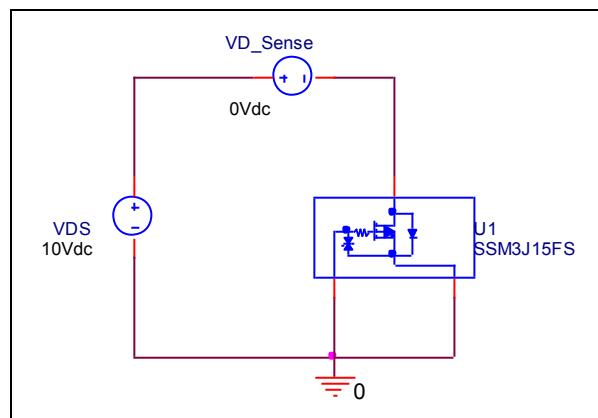


## Forward Current Characteristic

### Circuit Simulation Result

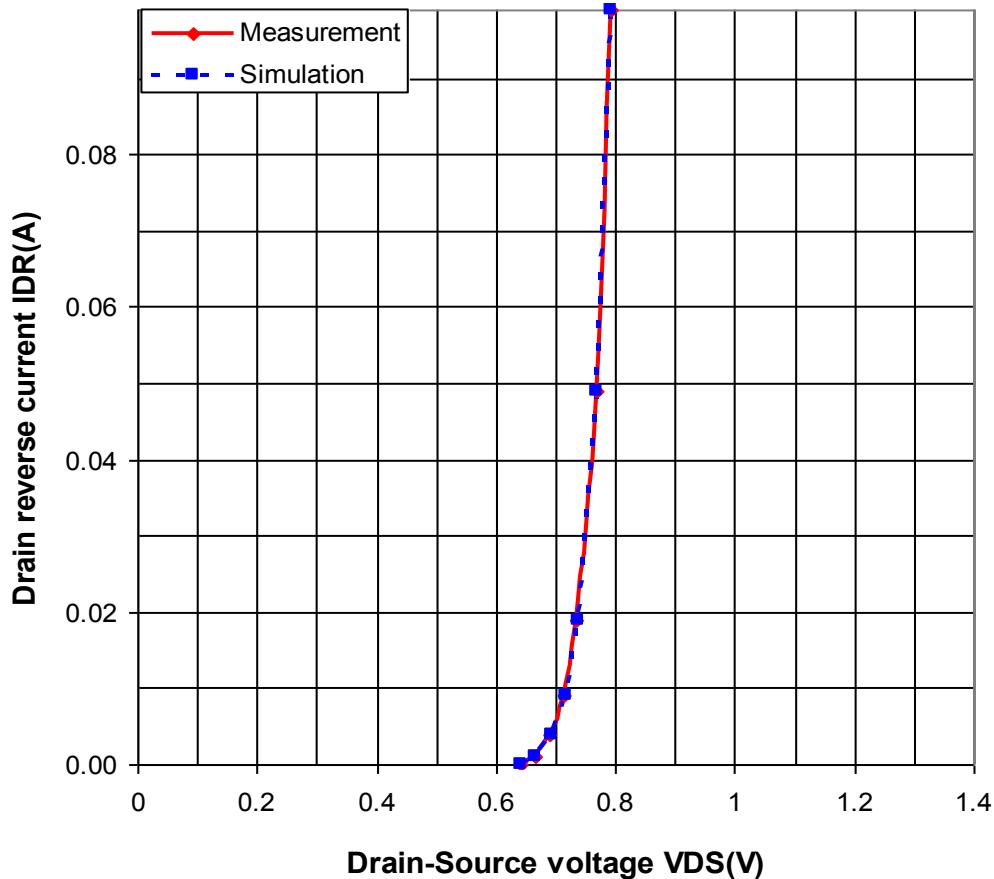


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

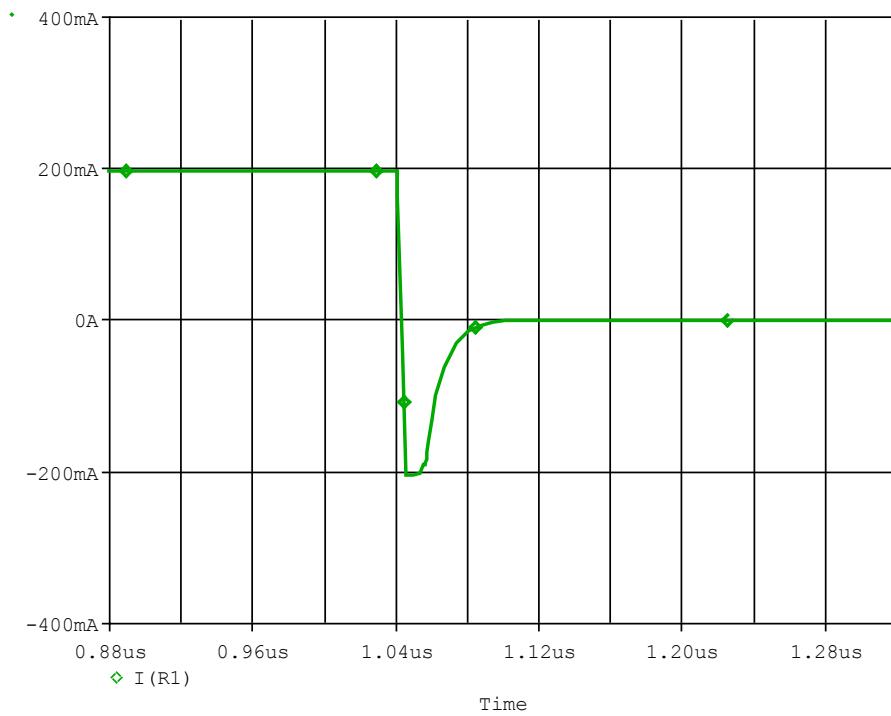


Simulation Result

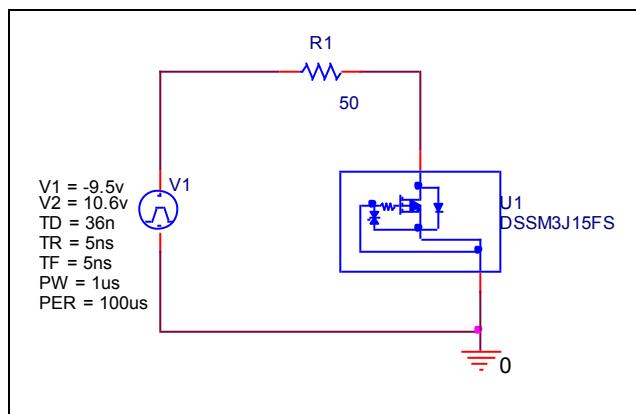
IDR(A)	VDS(V) Measurement	VDS(V) Simulation	%Error
0.001	0.642	0.643	0.156
0.002	0.665	0.666	0.150
0.005	0.690	0.692	0.290
0.010	0.715	0.716	0.140
0.020	0.736	0.737	0.136
0.050	0.768	0.767	-0.130
0.100	0.794	0.794	0.000

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit

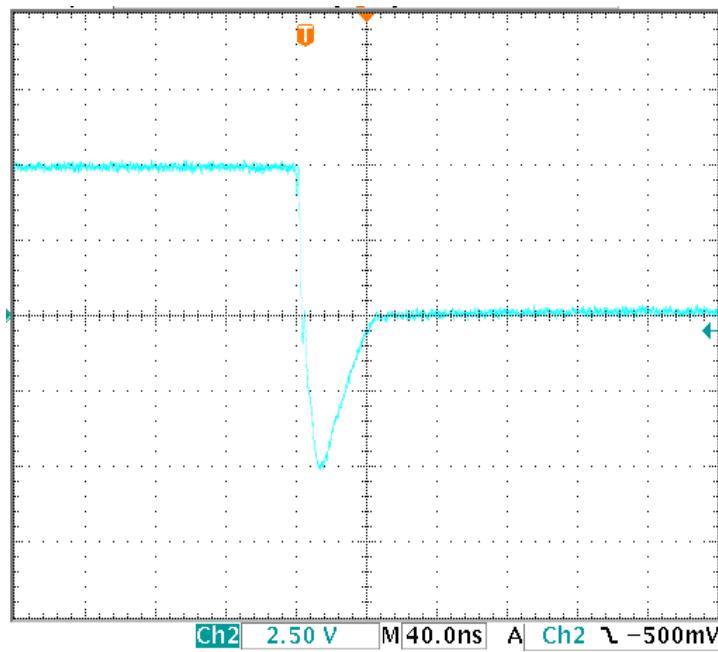


### Simulation Result

	Measurement	Simulation	Error (%)
$Trj(ns)$	<b>10.400</b>	<b>10.450</b>	<b>0.481</b>
$Trb(ns)$	<b>24.000</b>	<b>24.299</b>	<b>1.246</b>
$Trr(ns)$	<b>34.400</b>	<b>34.749</b>	<b>1.015</b>

## Reverse Recovery Characteristic

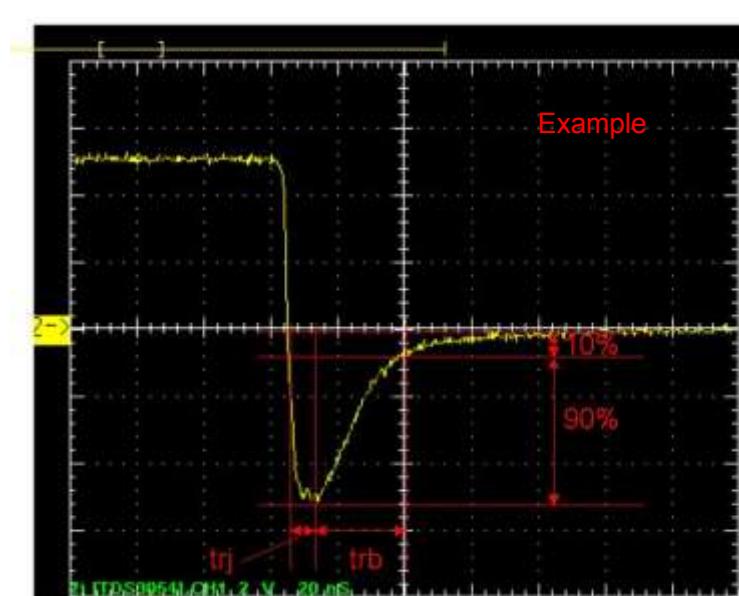
Reference



Trj=10.4(ns)

Trb=24(ns)

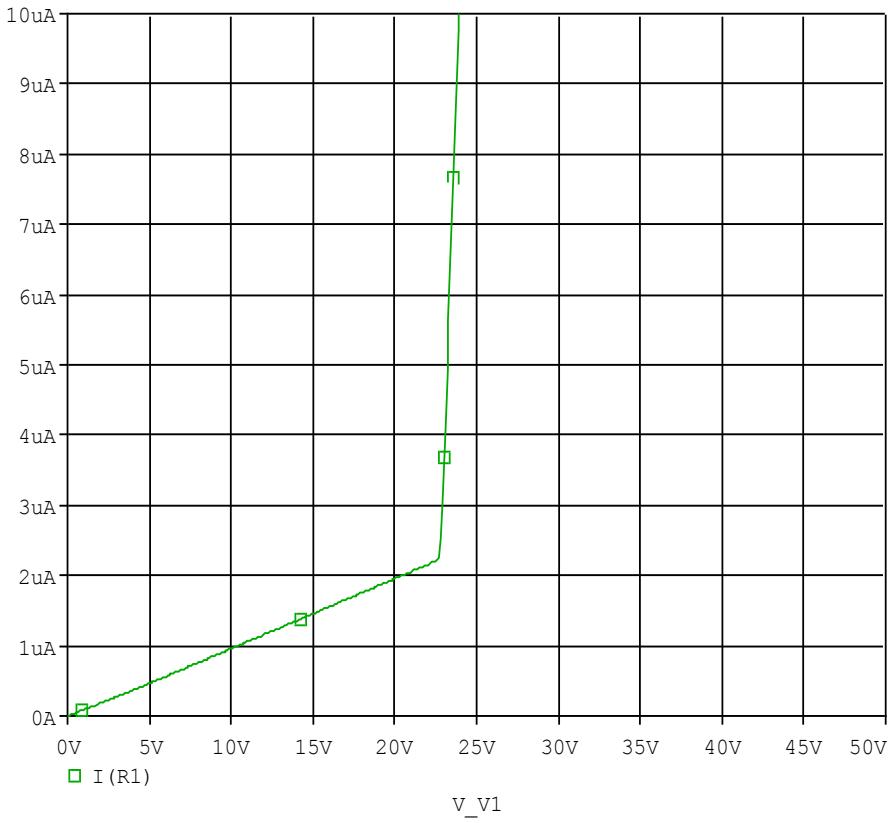
Conditions: Ifwd=Irev=0.04(A), Rl=50



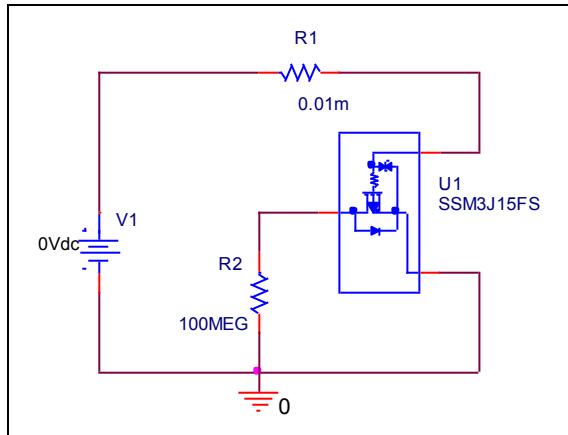
Relation between trj and trb

## Zener Voltage Characteristic

### Circuit Simulation Result



### Evaluation Circuit



## Zener Voltage Characteristic

## Reference

